Product data sheet

1. General description

Planar passivated AC Thyristor Triac power switch in a SOT186A (TO-220F) "full pack" plastic package with self-protective capabilities against low and high energy transients.

2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- Full cycle AC conduction
- Isolated mounting base package
- Less sensitive gate for high noise immunity
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Safe clamping capability for low energy over-voltage transients
- Self-protective turn-on during high energy voltage transients
- · Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls
- Applications subject to high temperature

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	-	-	120	A
T _j	junction temperature		-	-	125	°C
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 57$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	12	Α





Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{PP}	peak pulse voltage	T _j = 25 °C; non-repetitive, off-state; Fig. 6		-	-	2	kV
Static char	acteristics						
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G+;}$ $T_j = 25 \text{ °C; } Fig. 8$		-	-	35	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; } Fig. 8$		-	-	35	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD- G-;}$ $T_j = 25 \text{ °C; } Fig. 8$		-	-	35	mA
V_{CL}	clamping voltage	I_{CL} = 0.1 mA; t_p = 1 ms; T_j = 25 °C		850	-	-	V
Dynamic cl	haracteristics						
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _j = 125 °C; exponential 3000 waveform; gate open circuit			-	-	V/µs
dI _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit		14	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2		G sym051
3	G	gate		·
mb	n.c.	mounting base; isolated		
			TO-220F (SOT186A)	

6. Ordering information

Table 3. Ordering information

Type number	Package							
	Name	Description	Version					
ACTT12X-800C	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A					

ACTT12X-800C

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AC Thyristor Triac power switch

7. Marking

Table 4. Marking codes

Type number	Marking code
ACTT12X-800C	ACTT12X-800C

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 57$ °C; Fig. 1; Fig. 2; Fig. 3	-	12	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	-	120	A
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	132	А
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	72	A ² s
dl _T /dt	rate of rise of on-state current	I_T = 12 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s	-	100	A/µs
I _{GM}	peak gate current	t = 20 μs	-	2	Α
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C
V_{PP}	peak pulse voltage	T _j = 25 °C; non-repetitive, off-state; Fig. 6	-	2	kV

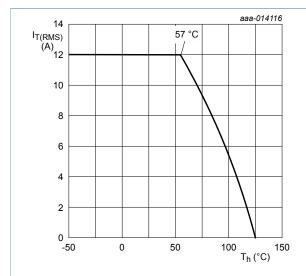


Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values

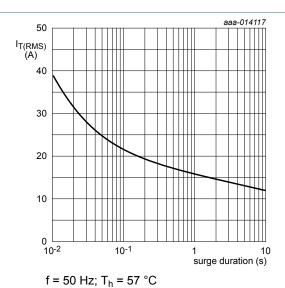


Fig. 2. RMS on-state current as a function of surge duration; maximum values

AC Thyristor Triac power switch

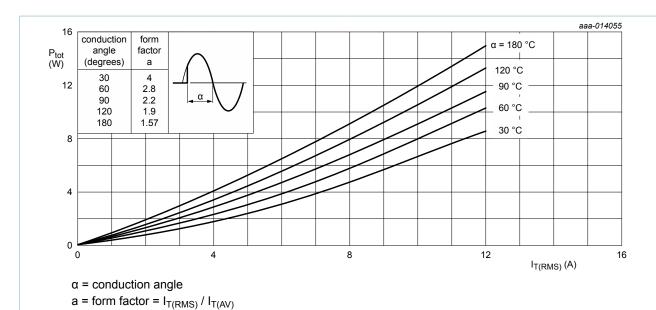


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

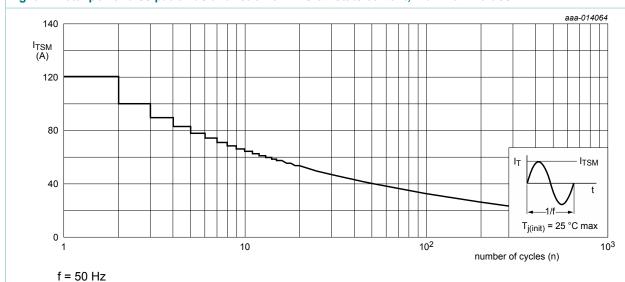


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

AC Thyristor Triac power switch

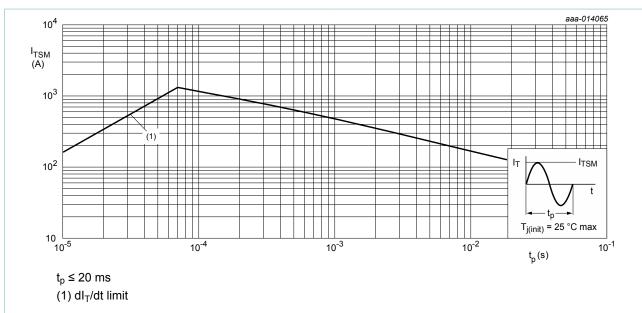


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

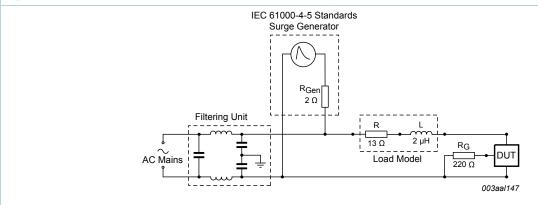
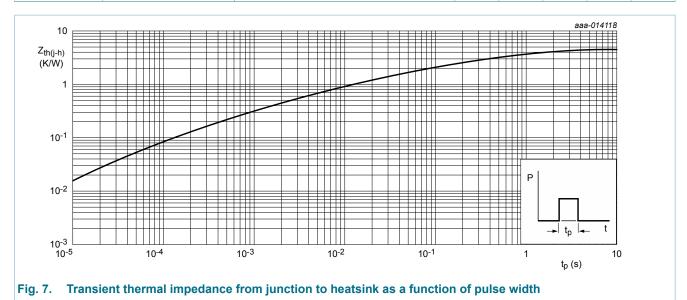


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	full cycle; with heatsink compound; Fig. 7		-	-	4.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		-	55	-	K/W



10. Isolation characteristics

Table 7. Isolation characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65% RH; T _h = 25 °C; from all terminals to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V	
C _{isol}	isolation capacitance	f = 1 MHz; T _h = 25 °C; from main terminal 2 to external heatsink		-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G+;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	35	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	35	mA
		V_D = 12 V; I_T = 100 mA; LD- G-; T_j = 25 °C; <u>Fig. 8</u>	-	-	35	mA
I _L latching current	latching current	$V_D = 12 \text{ V}; I_G = 100 \text{ mA}; LD+ G+;$ $T_j = 25 \text{ °C}; Fig. 9$	-	-	50	mA
		$V_D = 12 \text{ V; } I_G = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; } Fig. 9$	-	-	70	mA
		$V_D = 12 \text{ V}; I_G = 100 \text{ mA}; \text{LD- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{Fig. 9}$	-	-	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 10</u>	-	-	50	mA
V _T	on-state voltage	I _T = 17 A; T _j = 25 °C; <u>Fig. 11</u>	-	1.25	1.5	V
V_{GT}	gate trigger voltage	V _D = 12 V; I _T = 100 mA; T _j = 25 °C; Fig. 12	-	0.8	1	V
		V _D = 400 V; I _T = 100 mA; T _j = 125 °C; Fig. 12	0.2	0.45	-	V
I _D	off-state current	V _D = 800 V; T _j = 25 °C	-	-	10	μΑ
		V _D = 800 V; T _j = 125 °C	-	-	0.5	mA
V _{CL}	clamping voltage	I _{CL} = 0.1 mA; t _p = 1 ms; T _j = 25 °C	850	-	-	V
Dynamic cl	naracteristics		l			
dV _D /dt	rate of rise of off-state voltage	$V_{\rm DM}$ = 536 V; T _j = 125 °C; exponential 3000 waveform; gate open circuit		-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	14	-	-	A/ms

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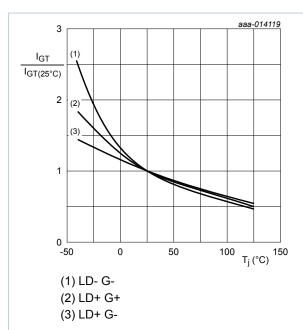


Fig. 8. Normalized gate trigger current as a function of junction temperature

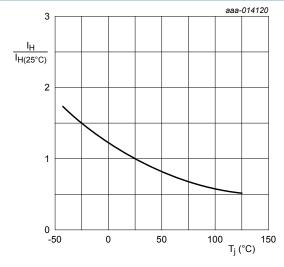


Fig. 10. Normalized holding current as a function of junction temperature

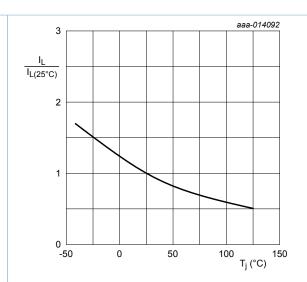
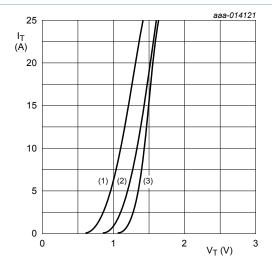


Fig. 9. Normalized latching current as a function of junction temperature



 $V_0 = 1.025 \text{ V}; R_s = 0.028 \Omega$

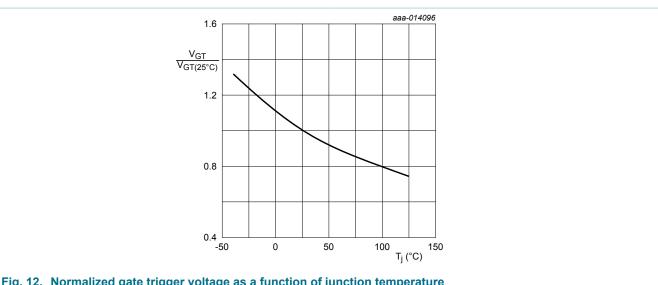
(1) T_i = 125 °C; typical values

(2) T_i = 125 °C; maximum values

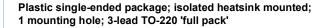
(3) T_i = 25 °C; maximum values

Fig. 11. On-state current as a function of on-state voltage

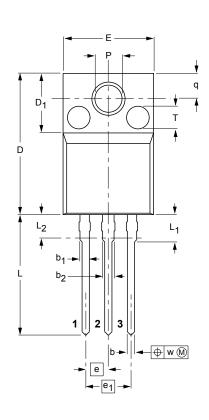
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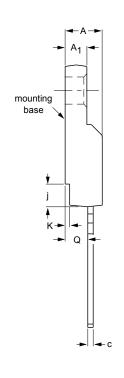


12. Package outline



SOT186A





0 5 10 mm

DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	b	b ₁	b ₂	С	D	D ₁	E	е	e ₁	j	K	L	L ₁	L ₂ ⁽¹⁾ max.	Р	Q	q	T ⁽²⁾	w
mm	4.6 4.0	2.9 2.5	0.9 0.7	1.1 0.9	1.4 1.0	0.7 0.4	15.8 15.2	6.5 6.3	10.3 9.7	2.54	5.08	2.7 1.7	0.6 0.4	14.4 13.5	3.30 2.79	3	3.2 3.0	2.6 2.3	3.0 2.6	2.5	0.4

Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are # 2.5×0.8 max. depth

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT186A		3-lead TO-220F				02-04-09 06-02-14	

Fig. 13. Package outline TO-220F (SOT186A)

ACTT12X-800C

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14. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	3
8	Limiting values	4
9	Thermal characteristics	7
10	Isolation characteristics	7
11	Characteristics	8
12	Package outline	11
13	Legal information	12
13.1	Data sheet status	
13.2	Definitions	12
13.3	Disclaimers	12
13.4	Trademarks	13

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